



**8N60-CBQ**

Preliminary

*Power MOSFET*

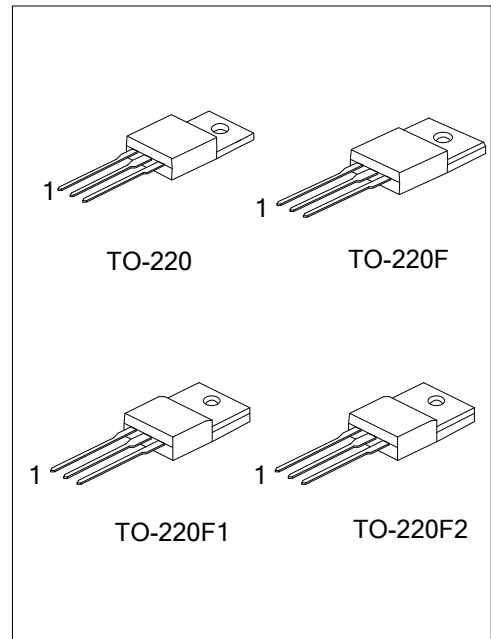
**8A, 600V N-CHANNEL  
POWER MOSFET**

■ DESCRIPTION

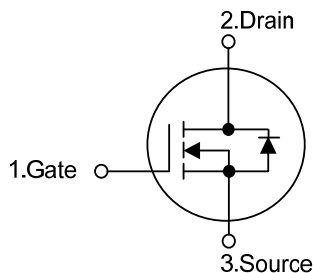
The UTC **8N60-CBQ** is a high voltage and high current power MOSFET, designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient AC to DC converters and bridge circuits.

■ FEATURES

- \*  $R_{DS(ON)} \leq 1.1\Omega @ V_{GS}=10V, I_D=4.0A$
- \* Fast switching capability
- \* Avalanche energy specified
- \* Improved dv/dt capability, high ruggedness



■ SYMBOL



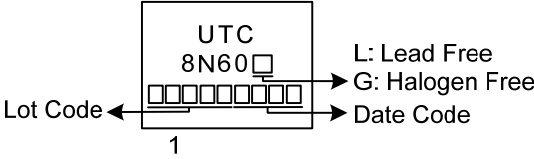
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
8N60L-TA3-T	8N60G-TA3-T	TO-220	G	D	S	Tube
8N60L-TF1-T	8N60G-TF1-T	TO-220F1	G	D	S	Tube
8N60L-TF2-T	8N60G-TF2-T	TO-220F2	G	D	S	Tube
8N60L-TF3-T	8N60G-TF3-T	TO-220F	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>8N60G-TA3-T</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) T: Tube (2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TF2: TO-220F2 (3) G: Halogen Free and Lead Free, L: Lead Free</p>
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MARKING



■ ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	600	V
Gate-Source Voltage		$V_{GSS}$	$\pm 30$	V
Drain Current	Continuous	$I_D$	8	A
	Pulsed (Note 2)	$I_{DM}$	32	A
Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	25	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220	$P_D$	200	W
	TO-220F/TO-220F1		48	W
	TO-220F2			
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Operating Temperature		$T_{OPR}$	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3.  $L = 0.8\text{mH}$ ,  $I_{AS} = 8\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$

4.  $I_{SD} \leq 8\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F	$\theta_{JA}$	62.5	$^\circ\text{C}/\text{W}$
	TO-220F1/TO-220F2			
Junction to Case	TO-220	$\theta_{JC}$	0.625	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		2.6	$^\circ\text{C}/\text{W}$
	TO-220F2			

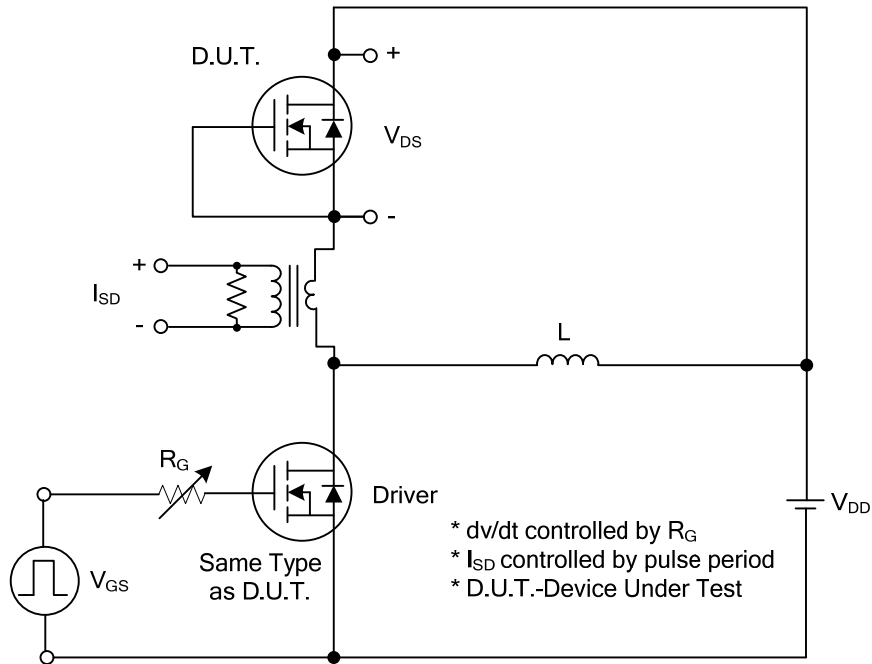
■ ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	600			V
Drain-Source Leakage Current	$I_{DSS}$	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$			10	$\mu\text{A}$
Gate-Source Leakage Current	Forward	$I_{GSS}$			100	nA
	Reverse				-100	nA
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		0.7		$\text{V}/^\circ\text{C}$
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	2.0		4.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{ V}, I_D = 4\text{ A}$			1.1	$\Omega$
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	$C_{ISS}$	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		350		pF
Output Capacitance	$C_{OSS}$			100		pF
Reverse Transfer Capacitance	$C_{RSS}$			4		pF
<b>SWITCHING CHARACTERISTICS</b>						
Total Gate Charge	$Q_G$	$V_{DS} = 50\text{ V}, V_{GS} = 10\text{ V}, I_D = 1.3\text{ A}$ $I_G = 100\ \mu\text{A}$ (Note 1, 2)		70		nC
Gate-Source Charge	$Q_{GS}$			6		nC
Gate-Drain Charge	$Q_{GD}$			3.5		nC
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD} = 30\text{ V}, V_{GS} = 10\text{ V},$ $I_D = 0.5\text{ A}, R_G = 25\ \Omega$ (Note 1, 2)		50		ns
Turn-On Rise Time	$t_R$			23		ns
Turn-Off Delay Time	$t_{D(OFF)}$			180		ns
Turn-Off Fall Time	$t_F$			33		ns
<b>DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS</b>						
Maximum Continuous Drain-Source Diode Forward Current	$I_S$				8	A
Maximum Pulsed Drain-Source Diode Forward Current	$I_{SM}$				32	A
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0\text{ V}, I_S = 8\text{ A}$			1.4	V
Reverse Recovery Time	$t_{rr}$	$V_{GS} = 0\text{ V}, I_S = 8\text{ A}$		285		ns
Reverse Recovery Charge	$Q_{rr}$	$di_F/dt = 100\text{ A}/\mu\text{s}$		2.6		$\mu\text{C}$

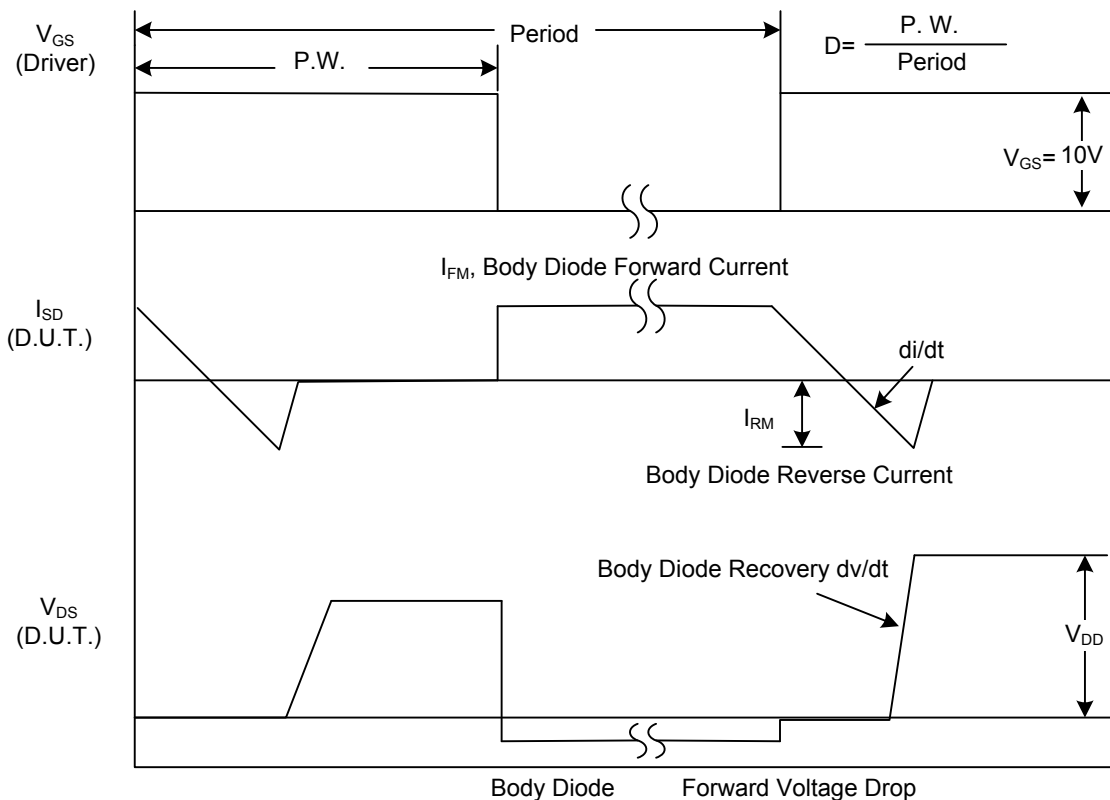
Notes: 1. Pulse Test: Pulse width  $\leq 300\ \mu\text{s}$ , Duty cycle  $\leq 2\%$ .

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

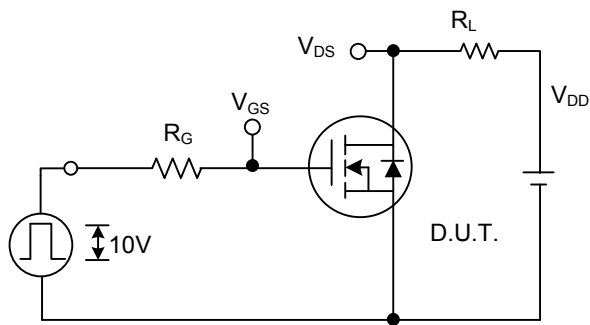


Peak Diode Recovery  $dv/dt$  Test Circuit

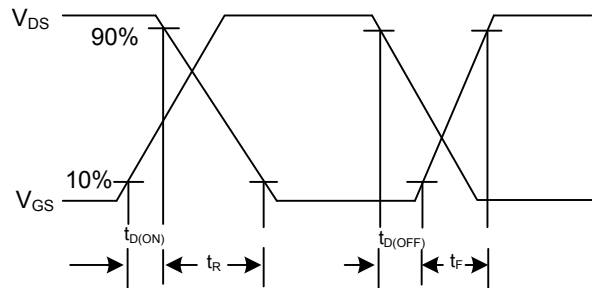


Peak Diode Recovery  $dv/dt$  Waveforms

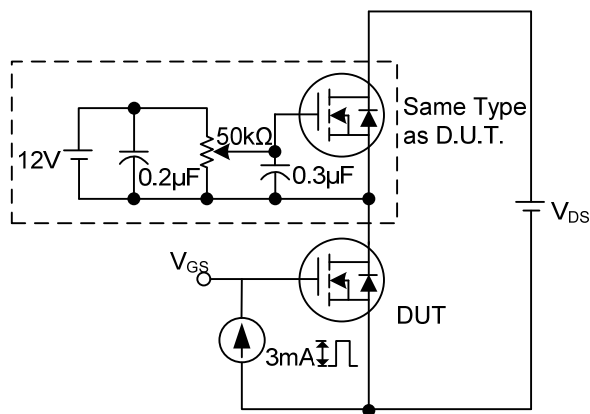
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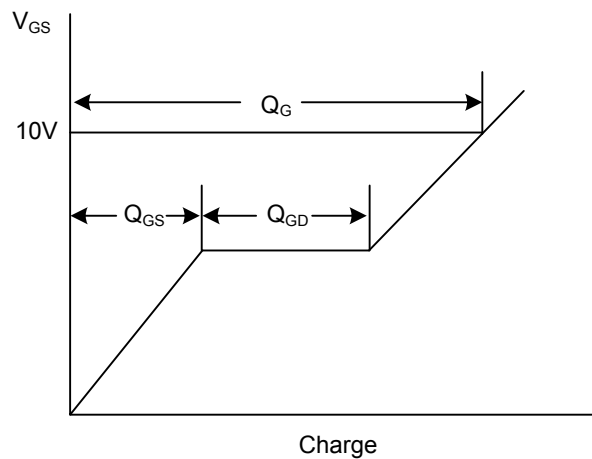
Switching Test Circuit



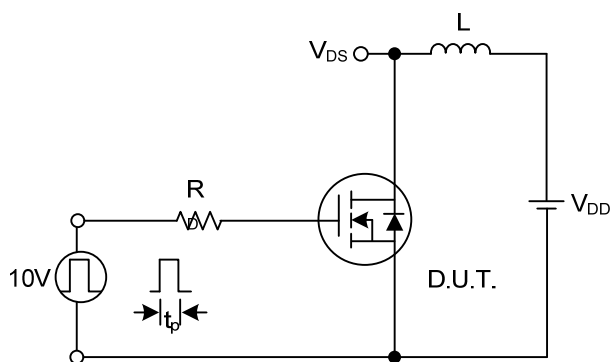
Switching Waveforms



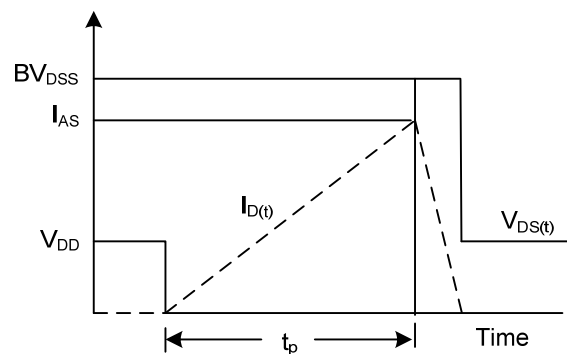
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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